



# CBCS SCHEME

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15TE73

Seventh Semester B.E. Degree Examination, Jan./Feb. 2023

## CMOS VLSI Design

Time: 3 hrs.

Max. Marks: 80

Note: Answer FIVE full questions, choosing ONE full question from each module.

### Module-1

- 1 a. Explain the NMOS enhancement mode transistor operation for different values of  $V_{GS}$  and  $V_{OS}$ . (08 Marks)
- b. Explain the CMOS inverter transfer characteristics highlighting the regions of operations of the MOS transistor. (08 Marks)

OR

- 2 a. With neat sketch, explain the CMOS p-well process steps to fabricate a CMOS inverter. (12 Marks)
- b. Compare CMOS and Bipolar transistor. (04 Marks)

### Module-2

- 3 a. With a neat diagram, explain  $\lambda$  based design rules for wired (nMOS and CMOS). (08 Marks)
- b. Draw the NMOS circuit diagram and stick diagram for the nMOS implementation of the Boolean expression  $y = AB + CD$ . (08 Marks)

OR

- 4 a. Derive the expression for sheet resistance  $R_s$ . (06 Marks)
- b. Derive an expression for the estimation of CMOS inverter delay. (10 Marks)

### Module-3

- 5 a. Derive the scaling factor for :
  - i) Saturation current
  - ii) Current density
  - iii) Power dissipation/unit area
  - iv) Maximum operation frequency. (08 Marks)
- b. Explain the General arrangement of 4 bit ALU. (08 Marks)

OR

- 6 a. With a neat diagram, explain  $4 \times 4$  Based shifter. (08 Marks)
- b. Explain Manchester Career's chain circuit. (08 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

**Module-4**

- 7 a. Discuss the architectural issues related to sub-system design. (08 Marks)  
b. Explain the structured design approach for the implementation of a parity generator with relevant stick diagram. (08 Marks)

**OR**

- 8 a. Explain switch logic implementation of a  $4 \times 4$  four way multiplexer. (08 Marks)  
b. Write short notes on FPGA architecture with a diagram. (08 Marks)

**Module-5**

- 9 a. Explain 3-transistor dynamic RAM-cell. (08 Marks)  
b. Explain write operation, read operation for four transistor dynamic and six transistor static CMOS memory cell. (08 Marks)

**OR**

- 10 a. List the system Timing Considerations. (08 Marks)  
b. Write short notes on Built in Self Test (BIST). (08 Marks)

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